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ABSTRACT OF THE DISCLOSURE

A hard mask material 2 such as a silicon oxide film is formed on an aluminum alloy film 3. The hard mask material 2 is patterned in the form of a thick film wiring 6, followed by etching the aluminum alloy film 3 to a given depth through the mask. A resist 5 applied to the thin film portion of the aluminum alloy film 3 is patterned in the form of a thin film wiring 7. Etching through the resist 5 and the hard mask material 2 as a mask is effected to form the thick film wiring 6 and the thin film wiring 7 in the same layer.